

| <b>L<br/>Number</b> | <b>Hits</b> | <b>S arch Text</b>  | <b>DB</b>   | <b>Tim stamp</b>    |
|---------------------|-------------|---|---|---------------------|
| -                   | 2           | (singl adj crystal).clm. and (amoprhiz r<br>am rphizing or amorphiz d or<br>amorphizati n).clm. and laser.clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:49 |
| -                   | 4526        | yamamoto and fujitsu  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:47 |
| -                   | 1           | (yamamoto and fujitsu) and (shallow and<br>deep).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:46 |
| -                   | 2           | yamamoto and tomonari and fujitsu   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:48 |
| -                   | 5353        | parasitic adj resistance  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:50 |
| -                   | 83          | (parasitic adj resistance) and (single adj<br>crystal).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:49 |
| -                   | 4           | ((parasitic adj resistance) and (single adj<br>crystal).clm.) and laser.clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:49 |
| -                   | 2           | (parasitic adj resistance).ti,ab,clm. and<br>(single adj crystal).ti,ab,clm. and<br>laser.ti,ab,clm. and ion.ti,ab,clm. and<br>(implant or implanting or implanted or<br>implantation).ti,ab,clm.                                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:52 |
| -                   | 1           | ((parasitic adj resistance).ti,ab,clm. and<br>(single adj crystal).ti,ab,clm. and<br>laser.ti,ab,clm. and ion.ti,ab,clm. and<br>(implant or implanting or implanted or<br>implantation).ti,ab,clm.) and<br>(amorphous).ti,ab,clm. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:52 |

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| - | 0   | ((parasitic adj r sistance).ti,ab,clm. and (single adj rystal).ti,ab,clm. and laser.ti,ab, lm. and i n.ti,ab, lm. and (implant r implanting r implanted or implantati n).ti,ab,clm.) and (oblique).ti,ab,clm.        | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:52 |
| - | 1   | ((parasitic adj resistance).ti,ab,clm. and (single adj crystal).ti,ab,clm. and laser.ti,ab,clm. and ion.ti,ab,clm. and (implant or implanting or implanted or implantation).ti,ab,clm.) and (oblique).ti,ab,clm.     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:52 |
| - | 2   | (parasitic adj resistance) and (single adj crystal) and laser and ion and (implant or implanting or implanted or implantation) and oblique and (amorphous or amorphize or amoprized or amorphizing or amorphization) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:53 |
| - | 38  | (single adj crystal) and (oblique near5 laser)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:56 |
| - | 0   | ((single adj crystal) and (oblique near5 laser)) and (parasitic near resistance)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:56 |
| - | 633 | (single adj crystal) and (oblique and laser)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:56 |
| - | 4   | ((single adj crystal) and (oblique and laser)) and (parasitic near resistance)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>11:57 |
| - | 13  | ((single adj crystal) same laser same (oblique or slanted or slanting or diagonal)).ti,ab,clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>12:51 |
| - | 1   | ((single adj crystal) same laser same (oblique or slanted or slanting or diagonal) same (ion) same (implant or implanted or implanting or implantation)).ti,ab,clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>12:51 |
| - | 1   | ((singl adj crystal) same las r same ( blique or slant d r slanting r diagonal) sam (i n) same (implant r implanted or implanting r implantation))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>12:51 |

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| - | 439 | ((ingle adj crystal) and laser and ( oblique or slanted or slanting or diagonal) and (ion) and (implant or implanted or implanting or implantation))   | USPAT;<br>US-P PUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>12:52 |
| - | 8   | ((single adj crystal) and laser and (oblique or slanted or slanting or diagonal) and (ion) and (implant or implanted or implanting or implantation))) and ((amorphize or amorphizing or amorphized or amorphization or amorphous) same oblique)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>12:52 |
| - | 6   | (parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and oblique  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:50 |
| - | 3   | (parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (oblique or slant or slanted or diagonal) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:52 |
| - | 21  | (parasitic near resistance) and (laser near (anneal or annealing or annealed or irradiation or irradiate or irradiating or irradiated)) and (ion near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:53 |
| - | 712 | ((ion near (implant or implanting or implanted or implantation)) near5 oblique)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:53 |
| - | 24  | ((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:54 |
| - | 2   | ((ion near (implant or implanting or implanted or implantation)) near5 oblique) same (amorphous or amorphize or amorphizing or amorphized) same (single adj crystal)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:54 |

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| - | 2   | ((i n near (implant r implanting or implanted r implantati n)) near5 bliqu ) sam (am rph us r am rphize or am rphizing r am rphized)) and (single adj crystal)                | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:55 |
| - | 31  | ((ion near (implant or implanting or implanted or implantation)) near5 oblique) and (amorphous or amorphize or amorphizing or amorphized)) and (single adj crystal)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:55 |
| - | 11  | ((ion near (implant or implanting or implanted or implantation)) near5 oblique) and (amorphous or amorphize or amorphizing or amorphized)) and (single adj crystal) and laser | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:56 |
| - | 1   | ((amorphize or amorphized or amorphous or amorphizing) near5 oblique near5 (ion or atom)).clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:57 |
| - | 1   | ((amorphize or amorphized or amorphous or amorphizing) near10 oblique near10 (ion or atom)).clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:57 |
| - | 14  | ((amorphize or amorphized or amorphous or amorphizing) near10 oblique near10 (ion or atom))   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:58 |
| - | 625 | (oblique near5 (ion or atom) near5 (implant or implantation or implantated or implantating))  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:59 |
| - | 82  | (oblique near5 (ion or atom) near5 (implant or implantation or implantated or implantating)).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:59 |
| - | 0   | (oblique near5 (ion or atom) near5 (implant or implantation or implantated or implantating)).clm. and laser.clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>14:59 |
| - | 7   | (oblique near5 (ion or atom) near5 (implant or implantation or implantated or implantating)).clm. and laser   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:00 |

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| - | 0     | ( oblique n ar5 (i n r at m) near5 (implant<br>r implantati n r implantat d r<br>implantating)).clm. and laser and (parasitic<br>n ar resistan e)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:00 |
| - | 14    | (oblique near5 (ion or atom) near5 (implant<br>or implantation or implantated or<br>implantating)).clm. and (single adj crystal)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:00 |
| - | 9     | (oblique near10 (ion or atom) near10<br>(implant or implantation or implantated or<br>implantating)) and (single adj crystal) and<br>laser   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:01 |
| - | 8     | (oblique near10 (ion or atom) near10<br>(implant or implantation or implantated or<br>implantating)) and (single adj crystal) and<br>laser and mask  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:01 |
| - | 2     | (oblique near10 (ion or atom) near10<br>(implant or implantation or implantated or<br>implantating)) and (single adj crystal) and<br>laser and mask and (parasitic near<br>resistance)                     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:02 |
| - | 10159 | ((atom or ion) near (implant or implanting or<br>implanted or implantation)).clm.  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:03 |
| - | 0     | ((atom or ion) near (implant or implanting or<br>implanted or implantation)).clm. and<br>oblique.clm. and (parasitic near resistance)<br>and (amorphous or amorphize or<br>amorphizing or amorphized).clm. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:04 |
| - | 12    | ((atom or ion) near (implant or implanting or<br>implanted or implantation)).clm. and<br>oblique.clm. and (amorphous or amorphize<br>or amorphizing or amorphized).clm.                                    | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:04 |
| - | 4     | ((atom or ion) near (implant or implanting or<br>implanted or implantation)).clm. and<br>oblique.clm. and (amorphous or amorphize<br>or amorphizing or amorphized).clm. and<br>(single adj crystal)        | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:06 |
| - | 2     | gate and source and drain and (single adj<br>crystal) and (insulating or dielectric) and<br>(atom or ion) and (amorphize or<br>am rphizing or amorphiz d) and oblique                                      | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:08 |

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| - | 1  | gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphize or amorphizing or amorphized) and oblique and laser  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:08 |
| - | 70 | gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:09 |
| - | 9  | gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask and (sidewall or (side near wall)) and junction and (impurity or impurities)                        | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:11 |
| - | 2  | gate and source and drain and (single adj crystal) and (insulating or dielectric) and (atom or ion) and (amorphous or amorphize or amorphizing or amorphized) and oblique and laser and (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed) and mask and (sidewall or (side near wall)) and junction and (impurity or impurities) and (shallow and deep) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:16 |
| - | 1  | gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphizing or amorphized or amorphize) and (seeping or seep or seeped)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:17 |
| - | 1  | gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:17 |
| - | 1  | gate and source and drain and (single adj crystal) and (shallow near junction) and (deep junction) and impurity and (atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:18 |

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| - | 1  | gate and source and drain and (single adjacent crystal) and (shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:18 |
| - | 1  | (shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped) and capacitance  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:18 |
| - | 1  | (shallow near junction) and (deep junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:18 |
| - | 1  | (shallow near junction) and (deep near junction) and (impurity or atom or ion) and (amorphous or amorphizing or amorphized or amorphize) and (seeping or seep or seeped)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:19 |
| - | 55 | (US-5569954-\$ or US-5824574-\$ or US-6001461-\$ or US-5709958-\$ or US-6534373-\$ or US-6391695-\$ or US-4597804-\$ or US-5955759-\$ or US-6458200-\$ or US-5698869-\$ or US-5291274-\$ or US-5229319-\$ or US-5908307-\$ or US-5736438-\$ or US-5514880-\$ or US-5693959-\$ or US-6610569-\$ or US-6524924-\$ or US-6455875-\$ or US-6315384-\$ or US-6267471-\$ or US-6180957-\$ or US-6133094-\$ or US-5962897-\$ or US-5930638-\$ or US-5793097-\$).did. or (US-6437367-\$ or US-6436815-\$ or US-5963278-\$ or US-5933205-\$ or US-5856228-\$ or US-5643806-\$ or US-5568288-\$ or US-5541124-\$ or US-5287205-\$ or US-6255146-\$ or US-6245622-\$ or US-6188085-\$ or US-6017781-\$ or US-5612230-\$ or US-5600154-\$ or US-5428237-\$ or US-5270227-\$ or US-5164806-\$ or US-6184088-\$).did. or (US-20020121654-\$ or US-20020073918-\$ or US-20020011627-\$).did. or (JP-2002280548-\$ or JP-2002329864-\$ or JP-63009152-\$ or JP-11087361-\$ or JP-09309713-\$ or JP-06267974-\$ or JP-05047794-\$).did. | USPAT;<br>US-PGPUB;<br>JPO                              | 2003/09/15<br>15:19 |

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| - | 1   | ((US-5569954-\$ r US-5824574-\$ or U -6001461-\$ r US-5709958-\$ r US-6534373-\$ r US-6391695-\$ or US-4597804-\$ r US-5955759-\$ or US-6458200-\$ r US-5698869-\$ r US-5291274-\$ or US-5229319-\$ or US-5908307-\$ or US-5736438-\$ or US-5514880-\$ or US-5693959-\$ or US-6610569-\$ or US-6524924-\$ or US-6455875-\$ or US-6315384-\$ or US-6267471-\$ or US-6180957-\$ or US-6133094-\$ or US-5962897-\$ or US-5930638-\$ or US-5793097-\$).did. or (US-6437367-\$ or US-6436815-\$ or US-5963278-\$ or US-5933205-\$ or US-5856228-\$ or US-5643806-\$ or US-5568288-\$ or US-5541124-\$ or US-5287205-\$ or US-6255146-\$ or US-6245622-\$ or US-6188085-\$ or US-6017781-\$ or US-5612230-\$ or US-5600154-\$ or US-5428237-\$ or US-5270227-\$ or US-5164806-\$ or US-6184088-\$).did. or (US-20020121654-\$ or US-20020073918-\$ or US-20020011627-\$).did. or (JP-2002280548-\$ or JP-2002329864-\$ or JP-63009152-\$ or JP-11087361-\$ or JP-09309713-\$ or JP-06267974-\$ or JP-05047794-\$).did.) and seeping seeping.clm. | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:19 |
| - | 271 |  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:19 |
| - | 5   | seeping.clm. and junction.clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:21 |
| - | 1   | (source and drain and gate and (single adj crystal) and (atom or impurity or ion) and (shallow adj junction) and (deep adj junction) and capacitance).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:22 |
| - | 1   | ((single adj crystal) and (atom or impurity or ion) and (shallow adj junction) and (deep adj junction) and capacitance).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:22 |



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|---|----|---|---|---------------------|
| - | 22 | ((shallow adj junction) and (deep adj junction)).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:23 |
| - | 5  | ((shallow adj junction) and (deep adj junction)).clm.) and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm.   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:24 |
| - | 2  | ((shallow adj junction) and (deep adj junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.                                       | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:25 |
| - | 3  | ((shallow near junction) and (deep near junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.                                     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:26 |
| - | 0  | ((shallow near junction) and (deep near junction)).clm. and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)).clm. and (amorphous or amorphize or amorphizing or amorphized).clm.) and oblique                        | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:25 |
| - | 1  | ((shallow near junction) and (deep near junction)) and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and laser and (single adj crystal) and oblique     | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:27 |
| - | 9  | ((shallow near junction) and (deep near junction)) and ((ion or atom or impurity) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and laser and (single adj crystal)                 | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:28 |
| - | 4  | (laser adj (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphize or amorphizing or amorphized) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:30 |

|   |     |   |   |                     |
|---|-----|---|---|---------------------|
| - | 4   | (laser adj (irradiate r irradiatig r irradiated or irradiati n or anneal or annealing or anneal d)) and blique and ((atom r impurity ri n) near (implant r implanting or implant d or implantation)) and (amotphous or amorphize or amorphizing or amorphized)  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:30 |
| - | 101 | (laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized)   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:30 |
| - | 4   | (laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction)              | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:31 |
| - | 4   | (laser adj (irradiate or irradiatig or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction) and oblique  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:32 |
| - | 4   | (laser adj (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single adj crystal) and ((deep or shallow) near junction) and oblique | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:32 |
| - | 5   | (laser near (irradiate or irradiating or irradiated or irradiation or anneal or annealing or annealed)) and oblique and ((atom or impurity or ion) near (implant or implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single bear crystal) and ((deep or shallow) near juncti n)           | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:33 |

|   |   |  |   |                     |
|---|---|--|---|---------------------|
| - | 4 | (laser n ar (irradiat or irradiating or irradiat d r irradiation or ann al r annealing r annealed)) and oblique and ((atom r impurity r i n) near (implant r implanting or implanted or implantation)) and (amorphous or amorphize or amorphizing or amorphized) and (single near crystal) and ((deep or shallow) near junction) | USPAT;<br>US-P PUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/09/15<br>15:35 |
|---|---|--|---|---------------------|